

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

1. (Currently amended) An etching solution for the production of integrated circuits comprising  
5- 20% by weight hydrofluoric acid,  
a solvent mixture consisting essentially of at least two ~~of which are selected from~~  
ethylene glycol, propylene glycol, ethanol, ~~or~~ and glycerol,  
and  
1-20 % by weight water.
2. (Canceled)
3. (Canceled)
4. (Currently amended) An etching solution according to Claim 1, comprising ~~as a~~  
solvent mixture consisting essentially of ethylene glycol and glycerol in a mixing ratio of from  
1:10 to 10:1.

5. (Currently amended) An etching solution according to Claim 1, comprising ~~as a~~ solvent mixture consisting essentially of ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.
6. (Canceled)
7. (Previously presented) An etching solution according to Claim 1, comprising a mixture of high-purity individual components.
8. (Withdrawn) A method for the selective etching of doped silicate layers comprising treating said doped silicate layers with an etching solution according to Claim 1.
9. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron doped glass.
10. (Withdrawn) A method according to claim 8, wherein said doped silicate is phosphorous doped glass.
11. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron-phosphorous doped glass.

12. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a spin etcher.
13. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a drip etcher.
14. (Currently amended) An etching solution according to claim 1, wherein the amount of said water is ~~from~~ 6.4 -20 % by weight.
15. (Currently amended) An etching solution comprising:  
5- 20% by weight hydrofluoric acid,  
a solvent mixture consisting essentially of at least two of ~~solvents selected from~~  
ethylene glycol, propylene glycol, ethanol, ~~or~~ and glycerol,  
and  
1-20 % by weight water  
for the etching of doped silicate layers.
16. (Currently amended) An etching solution comprising:  
5- 20% by weight hydrofluoric acid,  
a solvent mixture comprising at least two solvents at least two of ~~which are selected from~~  
~~from~~ ethylene glycol, propylene glycol, ethanol, ~~or~~ and glycerol,

and

1-20 % by weight water

for the etching of doped silicate layers.

17. (New) An etching solution for the production of integrated circuits consisting essentially of  
5- 20% by weight hydrofluoric acid,  
a solvent mixture consisting essentially of at least two of ethylene glycol, propylene glycol, ethanol, and glycerol,  
and  
1-20 % by weight water.
18. (New) An etching solution according to claim 17, wherein the amount of hydrofluoric acid is 10- 20% by weight .
19. (New) An etching solution according to claim 17, wherein the amount of hydrofluoric acid is 15- 20% by weight .